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Shou-Kong Fan

Filing Date: 04/18/01 Art Unit: 2818

Serial No.: 09/836,258 Docket No.: NAUP0280USA

10 Title: BYPASS CIRCUITS FOR REDUCING PLASMA DAMAGE

To: The Commissioner of Patents and Trademarks

Washington, D.C. 20231

Subject: Response to the Office Action dated 05/03 \$\frac{1}{2002}\$. 15

Dear Sir:

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AMENDMENT

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In response to the Office Action identified above, please amend the above-identified application as follows:

25 In the claims:

> 1. (Once amended) A bypass circuit for reducing plasma damage to a gate oxide of a metal-oxide semiconductor (MOS) wafer, the bypass circuit positioned on a semiconductor wafer, the semiconductor comprising a substrate, the MOS transistor, dielectric layer, and the bypass circuit, respectively, with the bypass circuit comprising: